









CEZ3R05

30V A 4.4mΩ A 86A A Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy PPAK5x6 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

MAXIMUM RATINGS

Parameter (T _C = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	30V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at R _{TH_JC}	I _D	86A
Continuous Drain Current at R _{TH_JA}	I _D	26A
Pulsed Drain Current at R _{TH_JC} Note 1	I _{DM}	344A
Pulsed Drain Current at R _{TH_JA} Note 1	I _{DM}	104A
Maximum Power Dissipation	P _D	83W
Single Pulsed Avalanche Energy Note 5	E _{AS}	57.8mJ
Single Pulsed Avalanche Current Note 5	I _{AS}	34A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

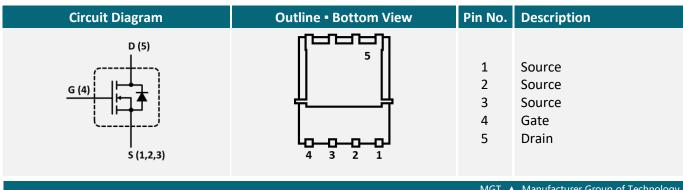
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	1.8°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH JA}	20°C/W

APPLICATIONS

Battery Managment	DC/DC	High Side	Low Side	Power
Systems	Converter	Switches	Switches	Banks
+ 4 -				4

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV_{DSS}	30			V
Zero Gate Voltage Drain Current	$V_{DS} = 30V$, $V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$, $V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = 250 \mu A$	$V_{GS(th)}$	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 30A$	R _{DS(ON)}		4.4	5.8	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 4.5V$, $I_D = 10A$	R _{DS(ON)}		5.7	7.5	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		1395		pF
Output Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		345		pF
Reverse Transfer Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C_{RSS}		215		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 1A, $R_{G(ext)}$ = 6Ω	t _{D(ON)}		14		ns
Turn-On Rise Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 1A, $R_{G(ext)}$ = 6Ω	t_{R}		7.2		ns
Turn-Off Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 1A, $R_{G(ext)}$ = 6Ω	t _{D(OFF)}		55		ns
Turn-Off Fall Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 1A, $R_{G(ext)}$ = 6Ω	t _F		11		ns
Total Gate Charge	V_{DD} = 15V, V_{GS} = 5V, I_D = 1A	Q_{G}		20		nC
Gate Source Charge	$V_{DD} = 15V$, $V_{GS} = 5V$, $I_D = 1A$	Q_{GS}		2.5		nC
Gate Drain Charge	$V_{DD} = 15V$, $V_{GS} = 5V$, $I_{D} = 1A$	Q_{GD}		8		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note3		I _S			69	А
Drain-Source Diode Forward Voltage Note3	$V_{GS} = 0V$, $I_S = 10A$	V_{SD}			1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 10 sec
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.
- 5: L = 0.1mH, $I_{AS} = 34$ A, $V_{DD} = 24$ V, $R_G = 25$ Ω, Starting $T_J = 25$ °C



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

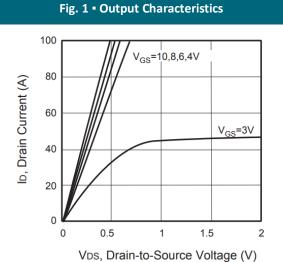


Fig. 2 • Transfer Characteristics

Fig. 3 - Capacitance

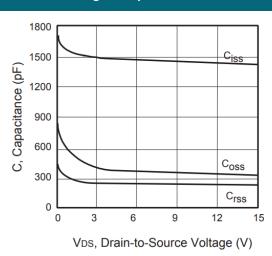


Fig. 4 • On-Resistance Variation with Temperature

Vgs, Gate-to-Source Voltage (V)

0

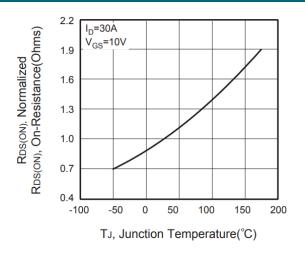


Fig. 5 • Gate Threshold Variation with Temperature

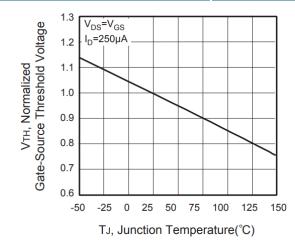
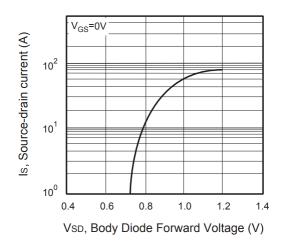


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

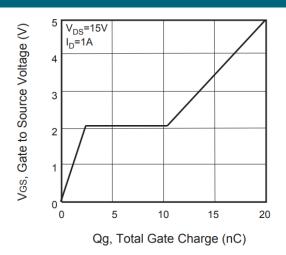


Fig. 8 • Maximum Safe Operating Area

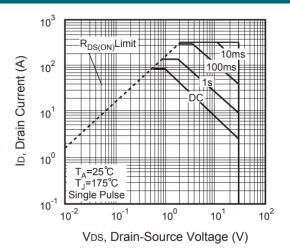
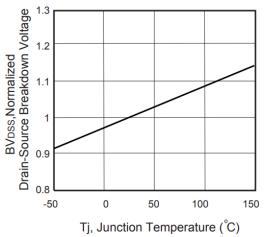
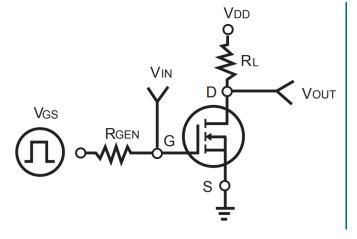
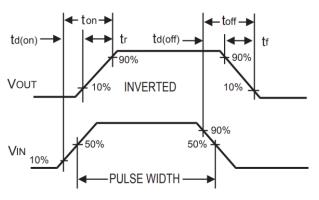


Fig. 9 • Breakdown Voltage Variation vs. Temperature





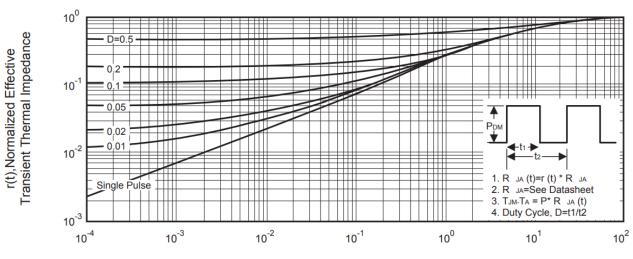






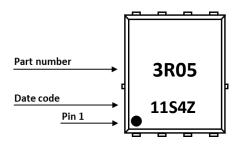
REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve



Square Wave Pulse Duration (sec)

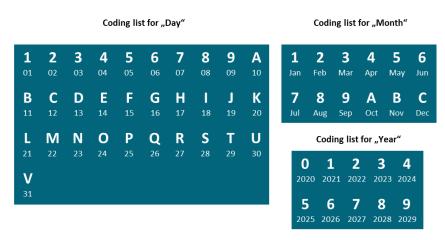
PART MARKING



DATE CODE

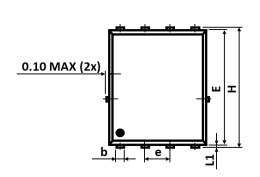
Example: 11S4Z

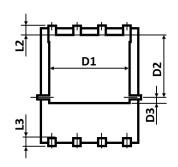


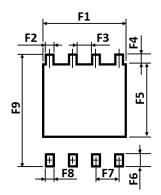


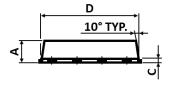


PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	0.800	-	1.170
b	0.340	-	0.490
С	0.200	-	0.340
D	4.800	-	5.100
D1	3.800	-	4.200
D2	3.180	-	3.780
D3	0.150	-	0.360

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
E	5.650	-	5.900
e		1.270 TYP	
Н	5.900	-	6.150
L1	0.050	-	0.250
L2	0.380	-	0.620
L3	0.380	-	0.750

Sym	Millimeters			
- 7,	(Min.)	(Typ.)	(Max.)	
F1	-	4.500	-	
F2	-	0.500	-	
F3	-	0.770	-	
F4	-	0.550	-	
F5	_	3.650	_	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F6	-	0.800	-
F7	-	1.270	-
F8	-	0.500	-
F9	-	6.250	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

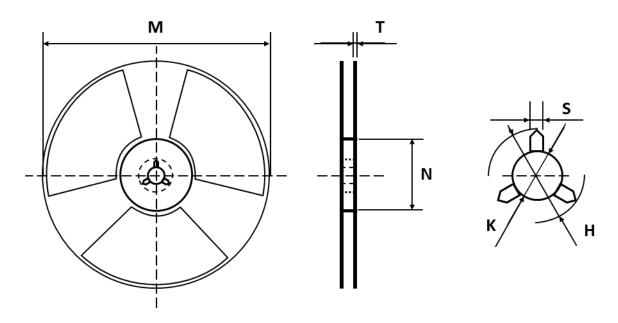
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEZ3R05	PPAK 5x6	Reel	2,500pcs	5,000pcs	40,000pcs

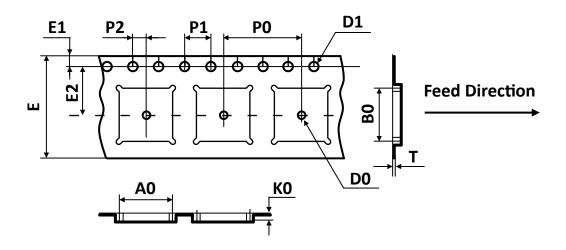


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

TAPE DIMENSIONS ▲ All dimensions in mm

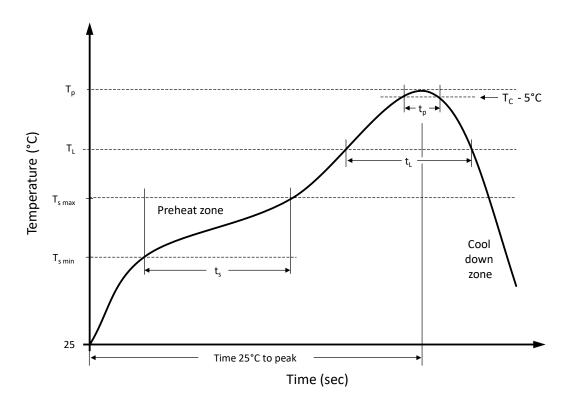


Package	Α0	В0	КО	D0	D1	Е	E1	E2	P0	P1	P2	T
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
PPAK 5x6	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t_L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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